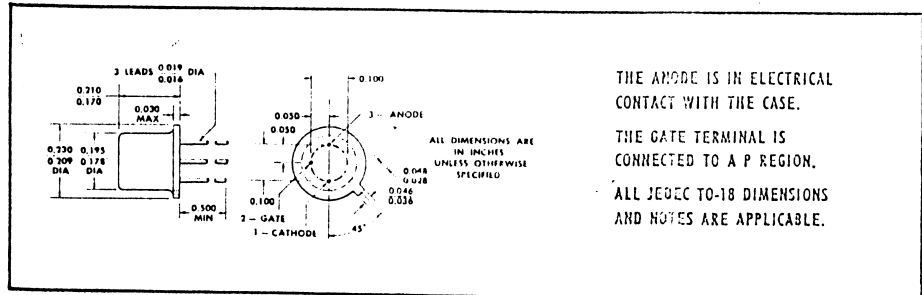


## P-N-P-N DIFFUSED SILICON REVERSE-BLOCKING TRIODE THYRISTOR

**\*mechanical data**



**\*absolute maximum ratings at (or below) 100°C case temperature (unless otherwise noted)**

		UNIT
Continuous Forward Blocking Voltage, $V_{FR}$ (See Note 1)	400	v
Continuous Reverse Blocking Voltage, $V_{RR}$ (See Note 2)	400	v
Continuous Anode Forward Current (See Note 3)	350	ma
Repetitive Peak Anode Forward Current (See Note 4)	20	a
Peak Anode Surge Current (See Note 5)	20	a
Peak Gate Reverse Voltage	5	v
Peak Gate Forward Current (Pulse width $\leq$ 8 msec)	250	ma
Operating Case Temperature Range	-65 to +150	°C
Storage Temperature Range	-65 to +150	°C
Lead Temperature $\frac{1}{16}$ Inch from Case for 10 Seconds	230	°C

- NOTES: 1. These values apply when the gate-cathode resistance  $R_{GK} \leq 1 k\Omega$ .  
 2. These values apply when the gate-cathode resistance  $R_{GK} \geq 1 k\Omega$ .  
 3. This value applies for continuous d-c operation with resistive load. Above 100°C derate according to Figure 1.  
 4. This value applies for square-wave pulses, PRR  $\geq$  60 pps, duty cycle  $\leq$  0.1%, when the device is operating at (or below) rated values of peak reverse blocking voltage and anode forward current.  
 5. This value applies for one 200- $\mu$ sec square wave when the device is operating at (or below) rated values of peak reverse blocking voltage and anode forward current. Surge may be repeated after the device has returned to original thermal equilibrium.

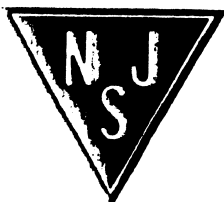
\*Indicates JEDEC registered data.

**\*electrical characteristics at 25°C case temperature (unless otherwise noted)**

PARAMETER	TEST CONDITIONS	MIN	MAX	UNIT
$I_{FR}$ Static Anode Forward Blocking Current	$V_F = \text{Rated } V_{FR}, R_{GK} = 1 k\Omega$		10	$\mu$ a
	$V_F = \text{Rated } V_{FR}, R_{GK} = 1 k\Omega, T_C = 125^\circ\text{C}$		100	$\mu$ a
$I_{RR}$ Static Anode Reverse Blocking Current	$V_R = \text{Rated } V_{RR}, R_{GK} = 1 k\Omega$		10	$\mu$ a
	$V_R = \text{Rated } V_{RR}, R_{GK} = 1 k\Omega, T_C = 125^\circ\text{C}$		100	$\mu$ a
$I_{GR}$ Gate Reverse Current	$V_{GR} = 2 \text{ v}, I_A = 0$		10	$\mu$ a
$I_{GT}$ Gate Trigger Current	$V_{AA} = 5 \text{ v}, R_L = 100 \Omega, PW_G \geq 10 \mu\text{sec}$		200	$\mu$ a
$V_{GT}$ Gate Trigger Voltage	$V_{AA} = 5 \text{ v}, R_L = 100 \Omega, PW_G \geq 10 \mu\text{sec}$	0.4	0.8	v
$I_H$ Holding Current	$V_{AA} = 5 \text{ v}, I_G = -150 \mu\text{a}$		5	ma
$V_F$ Forward Voltage	$I_F = 0.2 \text{ a}, R_{GK} \geq 1 k\Omega, \text{ See Note 6}$		1.5	v

NOTE 6: The initial instantaneous value is measured using pulse techniques. Anode-pulse width = 300  $\mu$ sec, PRR = 10 pps.

\*Indicates JEDEC registered data.



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